PIN Silicon Photodiode

OP913 Series



Features:

- TO-05 hermetically sealed package
- Linear response vs. irradiance
- Fast switching time
- · Narrow receiving angle
- Enhanced temperature range



Description:

OP913SL and OP913WSL consist of a PIN silicon photodiode mounted in a two-leaded TO-05 hermetically sealed package.

OP913SL has a dome lens with an acceptance angle of 10° when measured from the optical axis to the half power point. **OP913WSL** has a flat lens with an acceptance half angle of 30°. This large active area allows very low light level detection.

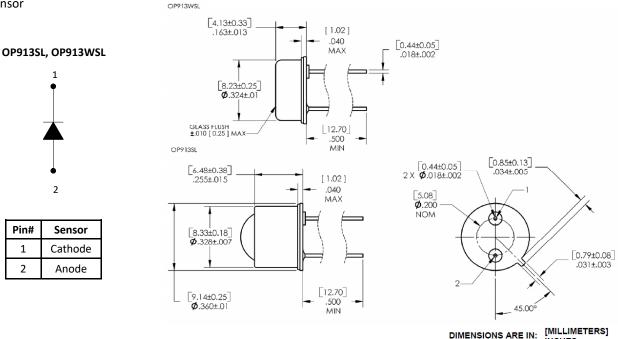
Please refer to Application Bulletin 210 for additional thermal design information.

Applications:

- Non-contact reflective object sensor
- Assembly line automation
- Machine automation
- Machine safety
- End of travel sensor
- Door sensor

Ordering Information Part Number Sensor Viewing Angle Lead Length Active Area OP913SL Photodiode 20° 0.50" 0.100x 0.100

OP913SL, OP913WSL





General Note

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Electrical Specifications

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

| Storage Temperature Range | -65° C to +150° C |
|--|-------------------|
| Operating Temperature Range | -65° C to +125° C |
| Reverse Voltage | 32 V |
| Lead Soldering Temperature [1/16 inch (1.6 mm) from the case for 5 seconds with soldering iron] (1) | 260° C |
| Power Dissipation ⁽²⁾ | 150 mW |

Electrical Characteristics (T_A = 25° C unless otherwise noted)

| SYMBOL | PARAMETER | MIN | TYP | MAX | UNITS | TEST CONDITIONS |
|------------------------------------|--|-----------|------------|--------|-------|---|
| I _L ⁽³⁾⁽⁴⁾ | Reverse Light Current: OP913SL OP913WSL | 120 40 | | - - | μΑ | $V_R = 5 \text{ V}, E_E = 5 \text{ mW/cm}^2$ |
| I _D ⁽³⁾ | Reverse Dark Current | - | - | 25 | nA | V _R = 10 V, E _E = 0 |
| V _{cc} | Open Circuit Voltage: OP913SL OP913WSL | | 400 300 | - | mV | E _E = 5 mW/cm ² |
| I _{sc} | Short Circuit Current: OP913SL OP913WSL | 120 40 | - | - | μΑ | E _E = 5 mW/cm ² |
| V_{BR} | Reverse Breakdown Voltage | 32 | - | - | V | Ε _Ε = 100 μΑ |
| Ст | Total Capacitance | - | - | 150 | pF | V _R = 0, E _E = 0, f = 1 MHz |
| t _{ON} , t _{OFF} | Turn On / Turn Off Time | - | 50 | - | ns | $V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega$ |

Notes:

- (1) RMA flux is recommended. Duration can be extended to a maximum of 10 seconds when flow soldering.
- (2) Derate linearly 1.30 mW/° C above 25° C.
- (3) Junction temperature for all devices in this data sheet is maintained at 25° C.
- (4) Light source is an unfiltered tungsten bulb operating at CT = 2870 K or equivalent infrared source.
- (5) At any particular wavelength the flux responsively, $R\theta$ is related to quantum efficiency by: $R\theta = \eta q (\lambda/1240)$, where ηq is the quantum efficiency in electrons per photon and λ is the wavelength in nanometers; thus at 900 nm, 0.60 A/W corresponds to a quantum efficiency of 83%.
- (6) NEP is the radiant flux at a specified wavelength, required for unity signal-to-noise ratio normalized for bandwidth. NEP calculation is made using responsivity at peak sensitivity wavelength, with spot noise measurement at 1000 Hz in a noise bandwidth of 6 Hz. (λ, f, Δ f) = (λp, 1000 Hz, 6 Hz).

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Typical Performance

OP913SL, OP913WSL

